

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max $T_A = +25^\circ\text{C}$
20V	28m Ω @ $V_{GS} = 4.5\text{V}$	7.63A
	41m Ω @ $V_{GS} = 2.5\text{V}$	4.35A

Description

This MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

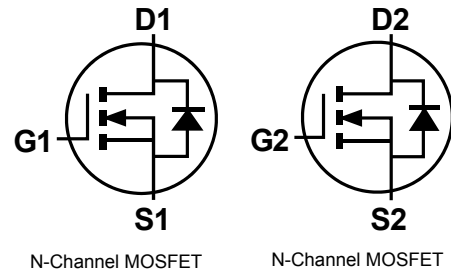
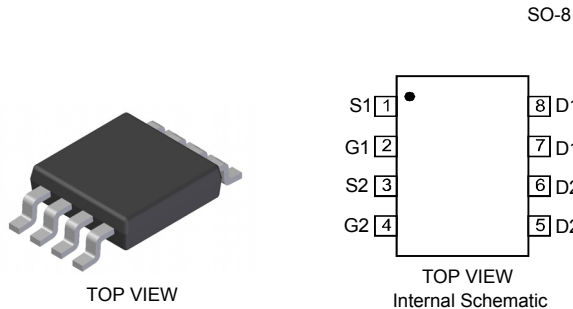
- Power Management Functions
- DC-DC Converters

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.072 grams (approximate)

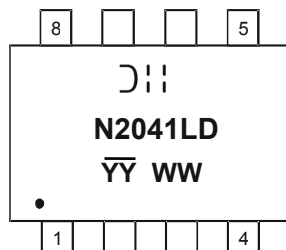
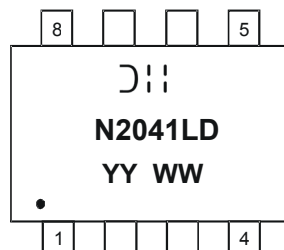


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041LSD-13	SO-8	2,500/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information


Chengdu A/T Site

Shanghai A/T Site

☺☺☺ = Manufacturer's Marking
 N2041LD = Product Type Marking Code
 YYWW = Date Code Marking
 YY or YY = Year (ex: 13 = 2013)
 WW = Week (01 - 53)
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
 YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	± 12	V
Drain Current (Note 5)	Steady State	$T_A = +25^\circ\text{C}$	I_D	7.63	A
		$T_A = +85^\circ\text{C}$		4.92	
Pulsed Drain Current (Note 6)			I_{DM}	30	A

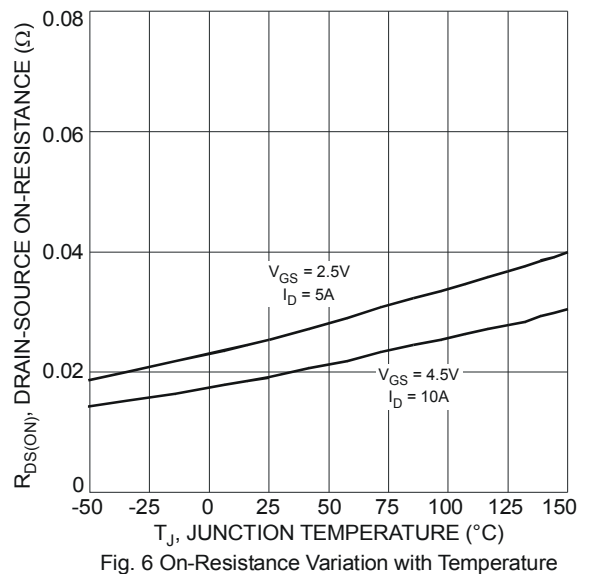
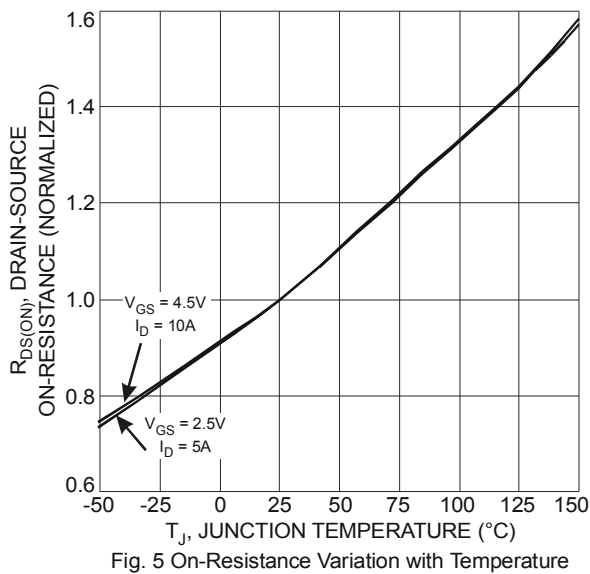
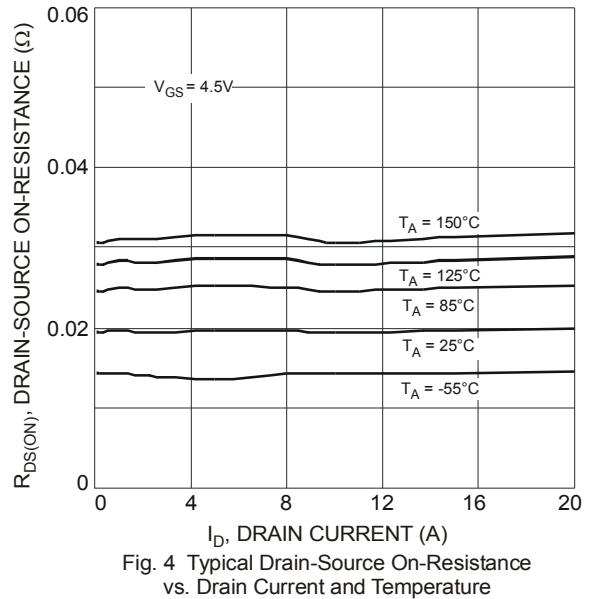
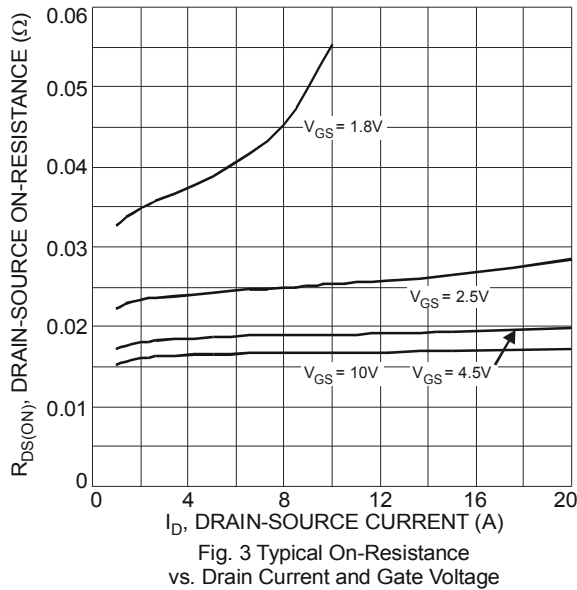
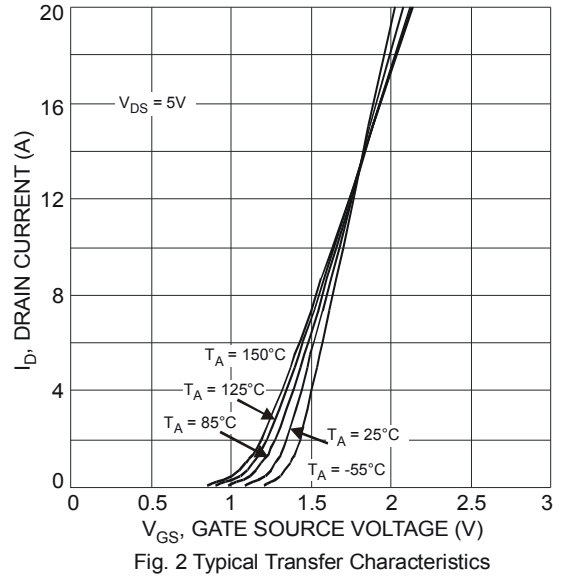
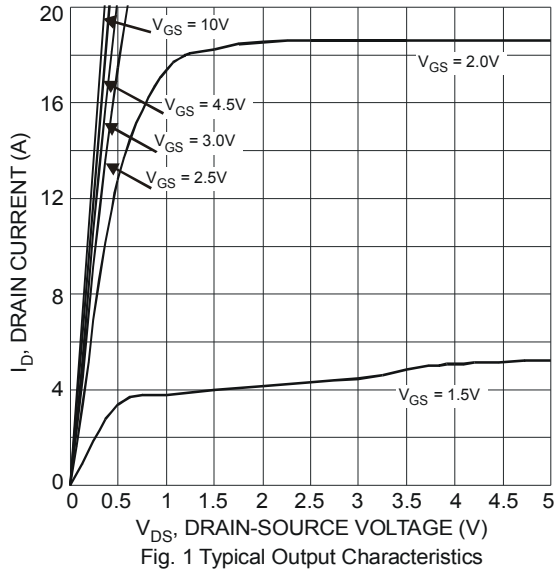
Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	1.16	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$	$R_{\theta JA}$	107.4	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	—	—	1	μA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.5	—	1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	19	28	m Ω	$V_{GS} = 4.5V, I_D = 6A$
			25	41		$V_{GS} = 2.5V, I_D = 5.2A$
Forward Transfer Admittance	$ Y_{fs} $	—	6	—	S	$V_{DS} = 10V, I_D = 6A$
Diode Forward Voltage	V_{SD}	—	0.7	1.2	V	$V_{GS} = 0V, I_S = 1.7A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	550	—	pF	$V_{DS} = 10V, V_{GS} = 0V, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	88	—		
Reverse Transfer Capacitance	C_{rss}	—	81	—		
Gate Resistance	R_g	—	1.34	—	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1\text{MHz}$
Total Gate Charge	Q_g	—	15.6	—	nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$
Total Gate Charge	Q_{gd}	—	7.2	—	nC	$V_{GS} = 4.5V, V_{DS} = 10V, I_D = 6A$
Gate-Source Charge	Q_{gs}	—	1	—		
Gate-Drain Charge	Q_{gd}	—	1.9	—		
Turn-On Delay Time	$t_{D(on)}$	—	4.69	—	ns	$V_{DD} = 10V, V_{GEN} = 4.5V, R_g = 1\Omega, I_D = 6.7A$
Turn-On Rise Time	t_r	—	13.19	—		
Turn-Off Delay Time	$t_{D(off)}$	—	22.1	—		
Turn-Off Fall Time	t_f	—	6.43	—		

- Notes:
- Device mounted on FR-4 PCB with minimum recommended pad layout.
 - Repetitive rating, pulse width limited by function temperature.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.



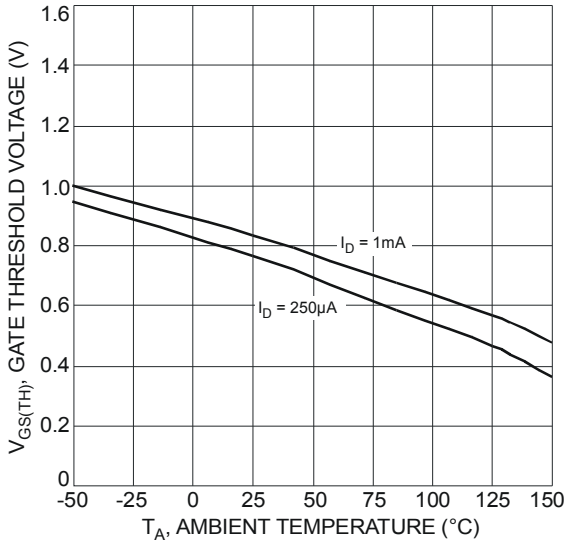


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

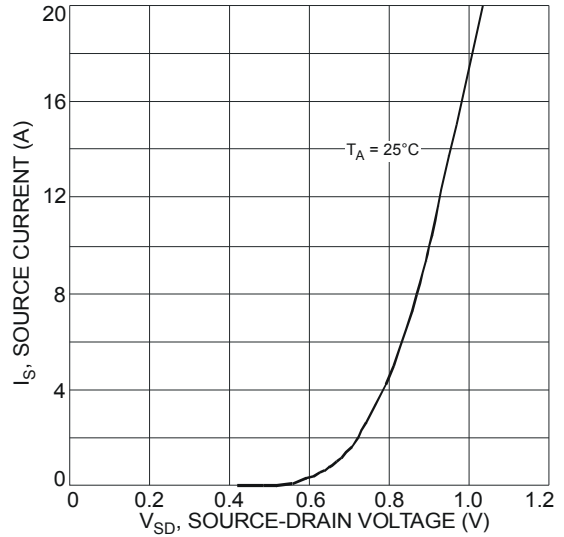


Fig. 8 Diode Forward Voltage vs. Current

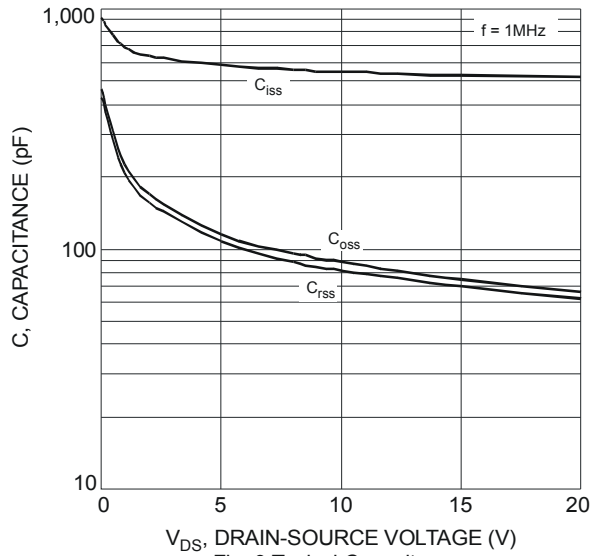


Fig. 9 Typical Capacitance

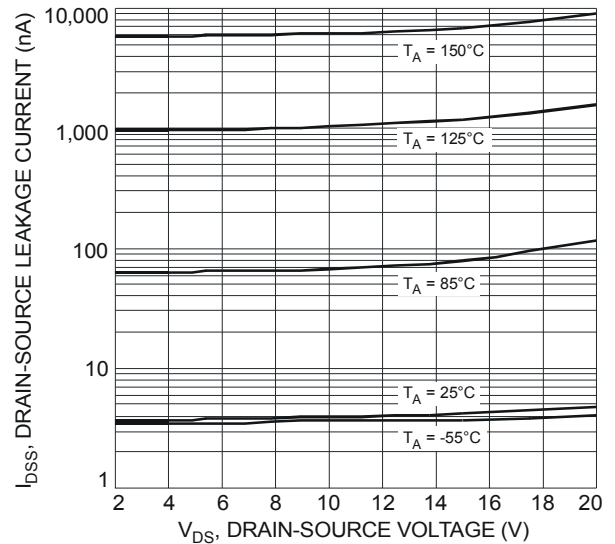


Fig. 10 Typical Drain-Source Leakage Current vs. Drain-Source Voltage

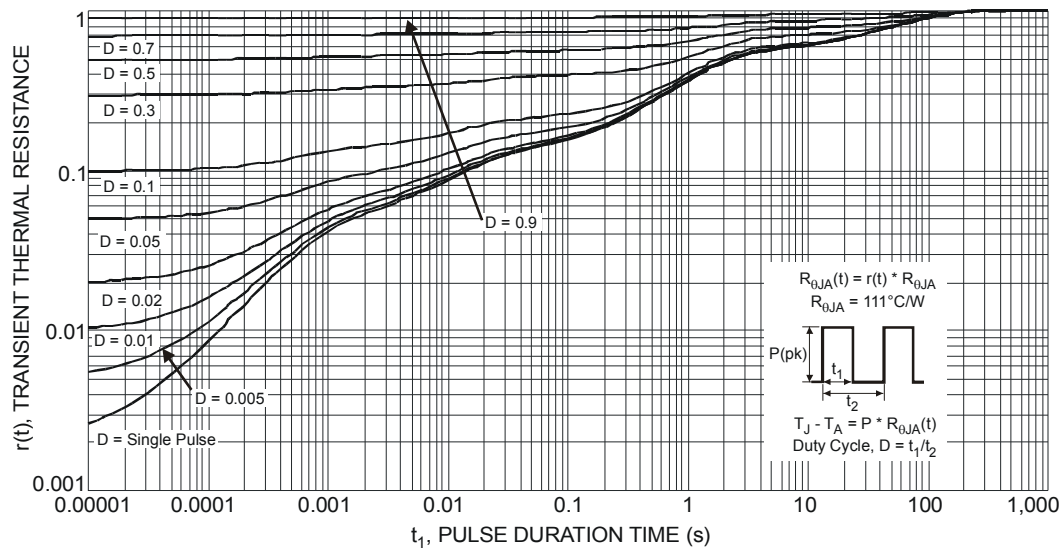
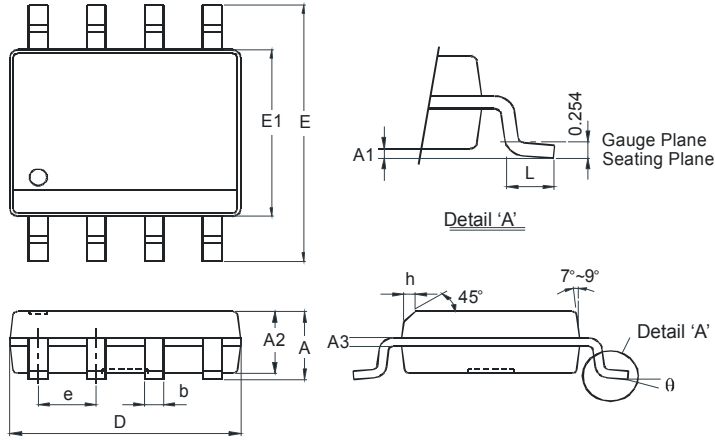


Fig. 11 Transient Thermal Response

Package Outline Dimensions

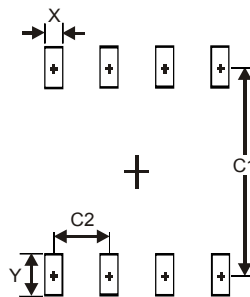
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SO-8		
Dim	Min	Max
A	-	1.75
A1	0.10	0.20
A2	1.30	1.50
A3	0.15	0.25
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.85	3.95
e	1.27 Typ	
h	-	0.35
L	0.62	0.82
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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